Front end for CD players BA6354BFS

The BA6354BFS is an analog front end LSI developed for CD players and CD-ROMs.

With a shared equalizer for normal and multiple speeds, and an input stage that supports hologram picks, the need for external components is minimized and the package size is greatly reduced.

Applications

CD players, car navigation CD-ROMs

Features

- 1) Supports hologram picks.
- 2) Internal APC circuit for laser control.
- 3) DC control enables balance adjustment for focus error and tracking error.
- Maintains the output amplitude at a constant value with an RF AGC circuit.
- 5) Switchable equalizer (internal normal speed and multiple speed equalizer).

● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Power supply voltage	Vcc	6	V
Power dissipation	Pd	850	mW
Operating temperature	Topr	-30 ∼+85	°C
Storage temperature	Tstg	−55∼+125	°C

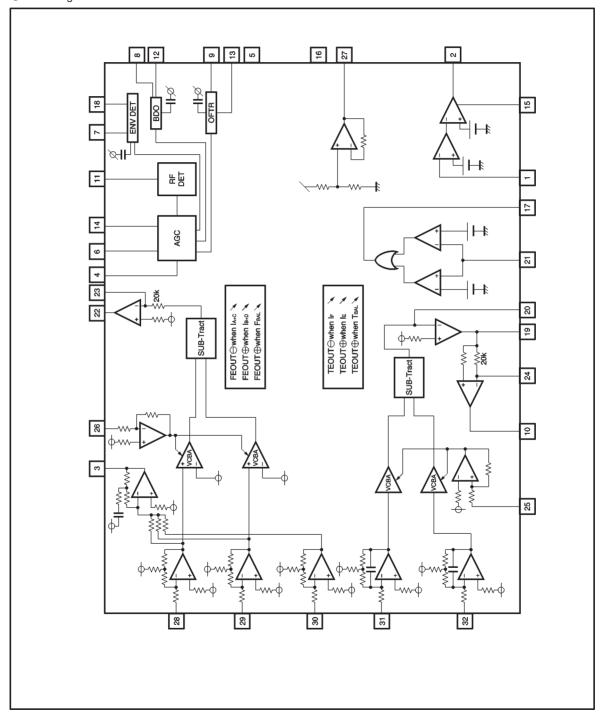
^{*} Reduced by 8.5mW for each increase inTa of 1°C over 25°C.

• Recommended operating conditions (Ta = 25°C)

Paramerter	Symbol	Limits	Unit
Power supply voltage	Vcc	3.4~5.5	V



■Block diagram



●Electrical characteristics (unless otherwise noted, Ta = 25°C, Vcc = 5V)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Quiescent current	lα	8	13	18	mA	
V _{ref} output voltage	Vref	2.2	2.5	2.8	٧	
⟨Focus error amplifier⟩						
Output offset voltage	VFEOF	-63	0	63	mV	
Balance crosstalk amount	VFEBC	-300	_	100	mV	V _{FB} =V _{ref} ±1V applied
I-V conversion gain	RFO	63	90	117	kΩ	V _{FB} =V _{ref}
I-V conversion relative gain	ΔRFO	-15	0	15	%	V _{FB} =V _{ref}
High level variable range 1	Вғ1н	0.21	0.35	0.49	_	V _{FB} =V _{ref} +1V
Low level variable range 1	B _{F1L}	1.19	1.70	2.21	-	V _{FB} =V _{ref} -1V
High level variable range 2	Вғ2н	1.19	1.70	2.21	-	V _{FB} =V _{ref} +1V
Low level variable range 2	B _{F2} L	0.21	0.35	0.49	_	V _{FB} =V _{ref} -1V
Frequency characteristics	GFO	-5.0	-3	-1.0	dB	f=1kHz, 30kHz
⟨Tracking error amplifier⟩						
Output offset voltage	VTROF	-63	0	63	mV	
Balance crosstalk amount	VTRBC	-200	_	200	mV	V _{TB} =V _{ref} ±1V applied
I-V conversion gain	RTR	420	600	780	kΩ	V _{TB} =V _{ref}
I-V conversion relative gain	ΔRTR	-15	0	15	%	V _{TB} =V _{ref}
High level variable range 1	Втін	0.21	0.35	0.49	_	V _{TB} =V _{ref} +1V
Low level variable range 1	Вт1	1.20	1.75	2.30	_	V _{TB} =V _{ref} -1V
High level variable range 2	Вт2н	1.20	1.75	2.30	_	V _{TB} =V _{ref} +1V
Low level variable range 2	Втаь	0.21	0.35	0.49	_	V _{TB} =V _{ref} -1V
Frequency characteristics	GTR	-5.0	-3	-1.0	dB	f=1kHz, 40kHz
⟨CROSS detector⟩						
CROSS output high level	Vcrh	4.2	_	_	V	V _{TB} =V _{ref} , f=2kHz
CROSS output low level	VCRL	_	_	0.8	٧	V _{TB} =V _{ref} , f=2kHz
⟨RF-AMP⟩						
Offset voltage	VRFOF	—75	0	75	mV	
I-V conversion gain	RrF	42.8	53.5	69.6	kΩ	
I-V conversion relative gain 1	∆ R _{RF1}	-10	0	10	%	
I-V conversion relative gain 2	Δ R _{RF2}	-10	0	10	%	
Frequency characteristics	GRF	-6.8	-2.8	0.2	dB	f=500kHz, 3MHz
EQ characteristics	ΔGEQ	-0.8	1.7	4.2	dB	f=1MHz, 1.5MHz

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
⟨AGC⟩						
AGC maximum gain	GAGC	10.0	14.5	19.0	dB	f=500kHz
AGC operating gain	GOPAGO	2.0	5.0	8.0	dB	f=500kHz, V _{IN} =500mV _{P-P}
AGC compression	GCMAGC	1.5	4.5	7.5	dB	f=500kHz, V _{IN} =100mV _{P-P}
AGC frequency characteristics	Grago	-3.0	0	3.0	dB	f=3MHz, VIN=500mV _{P-P}
(RFDET)						
RFDET detection level	VRFDET	0.091	0.130	0.175	V _{P-P}	f=500kHz (RFIN level)
RFDET high level	VRFH	4.2	_	_	V	f=500kHz (RFIN level)
RFDET low level	VRFL	_	_	0.8	٧	f=500kHz (RFIN level)
⟨BDO⟩						
BDO detection current	Івро	0.6	1.0	1.4	μΑ	
BDO high level	Vврон	4.2	_	_	٧	f=2kHz, rectangular wave
BDO low level	VBDOL	_	_	0.8	٧	f=2kHz, rectangular wave
⟨OFTR⟩						
OFTR detection current	loftr	0.6	1.0	1.4	μΑ	
OFTR high level	Voftrh	4.2	_	_	٧	f=2kHz, rectangular wave
OFTR low level	Voftrl	_	_	0.8	٧	f=2kHz, rectangular wave
(LD-APC)						
LD ON high level input	VLDH	3.5	_	_	٧	
LD OFF low level input	VLDL	_	_	1.5	٧	
LD ON operating voltage	V _{LD}	145	180	215	mV	DC sweep
⟨VDET detector⟩						
VDET detection level 1	V _{DET1}	56	80	104	mV	DC sweep
VDET detection level 2	V _{DET2}	-104	-80	-56	mV	DC sweep
VDET high level	VDETH	4.2	_	_	٧	DC sweep
VDET low level	VDETL	_	_	0.8	٧	DC sweep
⟨3T ENV⟩						
CEA-ENV propagation characteristics	GENV	21	23	25	dB	
CEA input impedance	RCEA	6.4	8.0	9.6	kΩ	
ENV output impedance	Renv	6.0	7.5	9.0	kΩ	
ENV-AMP offset voltage	VENVOF	-150	0	150	mV	
CEA-AMP operating voltage	VOPCEA	90	150	210	mV	

Measurement circuit

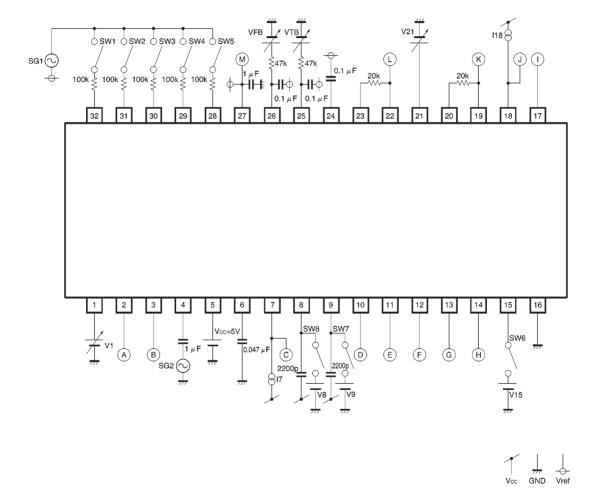
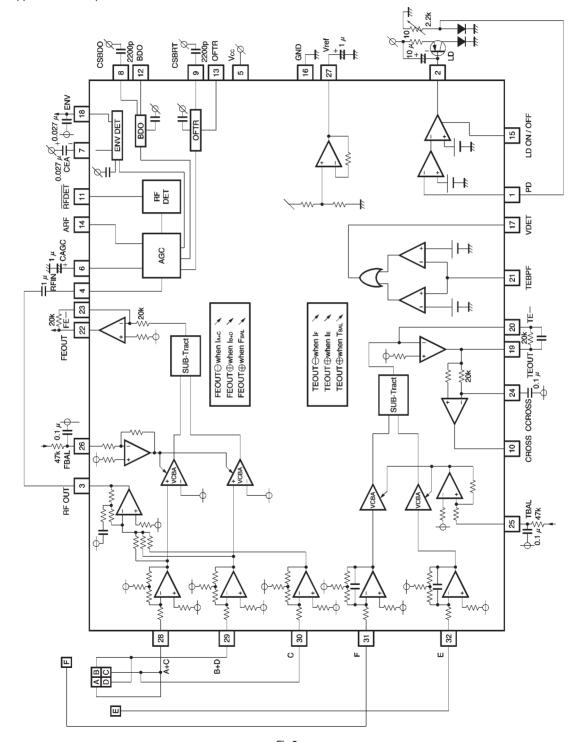


Fig.1

Application example



Electrical characteristics curve

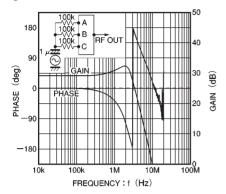


Fig.3 RFamplifier frequency characteristics

External dimensions (Units: mm)

